

23. (NEW) The method of claim 22 wherein the at least one second MEMS component is a hinge.

24. (NEW) The method of claim 23 wherein the at least one MEMS component is a mirror retained by the hinge.

25. (NEW) The method of claim 21 wherein depositing at least one layer of polysilicon includes chemical vapor deposition.

26. (NEW) The method of claim 25 wherein depositing at least one layer of polysilicon includes low pressure chemical vapor deposition.

27. (NEW) The method of claim 21 wherein forming at least one first MEMS component includes forming a deflecting mirror.

28. (NEW) The method of claim 27 further comprising forming at least one second MEMS component by patterning the polysilicon, the at least one second MEMS component including a hinge retaining the deflecting mirror.

29. (NEW) The method of claim 28 wherein forming at least one first MEMS component further includes forming a torsional mirror, and the method further comprises forming a recess in the SOI wafer and mounting a light emitter in the recess so that it will emit light at the deflecting mirror, which deflects light to the torsional mirror.

30. (NEW) A MEMS device comprising:

at least one single crystal silicon component bonded to an insulator that rests on a handle wafer; and

at least one polysilicon component derived from a layer of polysilicon applied over the at least one single crystalline silicon component.

31. (NEW) The MEMS device of claim 30 wherein the at least one single crystal silicon component comprises a deflecting mirror.

32. (NEW) The MEMS device of claim 31 wherein the at least one polysilicon component comprises a hinge retaining the deflecting mirror.

33. (NEW) The MEMS device of claim 30 wherein the at least one single crystal silicon component comprises a torsional mirror.

34. (NEW) The MEMS device of claim 30 wherein the at least one polysilicon component comprises a hinge.

35. (NEW) The MEMS device of claim 30 further comprising:

a recess in the handle wafer aligned with the at least one single crystal silicon component;
and

a semiconductor light emitter mounted in the recess and oriented to emit a light beam at the single crystal silicon component.

36. (NEW) The MEMS device of claim 35 wherein the at least one single crystal silicon component comprises a deflecting mirror at which the light beam is directed and a torsional mirror to which the deflecting mirror deflects the light beam, and the at least one polysilicon component comprises a hinge retaining the deflecting mirror.